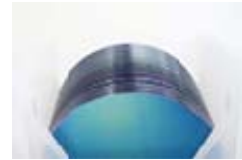




## Silicon Crystal & Compound Semiconductor

### Epitaxial (EPI) Silicon Wafer

**Epitaxial (EPI) Silicon Wafer** adopts chemical vapor deposition (CVD) technology to introduce crystal atoms and resulting mechanical stress at the precise depth of intended epi layer thickness. By temperature change controlling techniques, the multiple device layer patterns of epitaxial process can finally meet many advanced requirements in Microelectronics, Photonics or Photovoltaic industries. Homogeneous or heterogeneous epitaxial process is applicable, and 4" 5" or 6" can be supplied.



No.	Items		Standard Specifications		
1	General	Size	4"	5"	6"
		Diameter mm	100±0.5	125±0.5	150±0.5
		Orientation	<100> or <111>	<100> or <111>	<100> or <111>
2	Epitaxial Layer	Growth Method	CVD	CVD	CVD
		Conductivity Type	P, P+, N, N+	P, P+, N, N+	P, P+, N, N+
		Thickness μm	2.5-120	2.5-120	2.5-120
		Thickness Uniformity max	3%	3%	3%
		Resistivity Ω·cm	0.1-50	0.1-50	0.1-50
		Resistivity Uniformity	≤3%	≤5%	-
		Dislocation cm <sup>-2</sup>	<10	<10	<10
		Surface Quality	No chip, haze or orange peel remains, etc.		
		3	Handle Substrate	Growth Method	CZ
Conductivity Type	P/N			P/N	P/N
Thickness μm	525-675			525-675	525-675
Thickness Uniformity max	3%			3%	3%
Resistivity Ω·cm	As required			As required	As required
Resistivity Uniformity max	5%			5%	5%
TTV μm max	10			10	10
Bow μm max	30			30	30
Warp μm max	30			30	30
EPD cm <sup>-2</sup> max	100			100	100
Edge Profile	Rounded			Rounded	Rounded
Surface Quality	No chip, haze or orange peel remains, etc.				
Back Side Finish	Etched or LTO (5000±500Å)				
4	Packing	Cassette inside, carton box outside			